



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-523 Plastic-Encapsulate Diode

DAP222 SWITCHING DIODE

FEATURES:

Power dissipation

P_D : 150 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_F : 100 mA

Collector-base voltage

V_R : 80 V

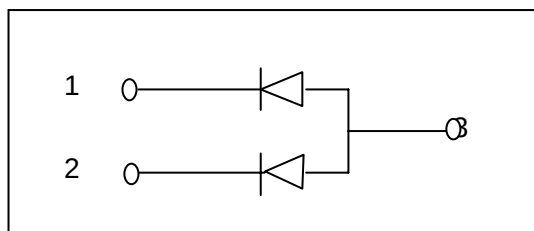
Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-523



CIRCUIT:



MARKING: P

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse voltage leakage current	I_R	$V_R=70V$		0.1	μA
Forward voltage	V_F	$I_F=100mA$		1.2	V
Diode capacitance	C_D	$V_R=6V, f=1MHz$		3.5	pF
Reverse recovery time	t_{rr}	$V_R=6V, I_F=5mA$		4	ns